

# PSMN4R6-60PS

# N-channel 60 V, 4.6 m $\Omega$ standard level MOSFET in TO220

Rev. 3 — 18 April 2012

**Product data sheet** 

### 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in a TO-220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

### 1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$		-	-	60	V
$I_D$	drain current	T <sub>mb</sub> = 25 °C; see <u>Figure 1</u>	[1]	-	-	100	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	211	W
Tj	junction temperature			-55	-	175	°C
Static characte	eristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ °C};$ see Figure 12		-	8.05	10.6	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13		-	3.5	4.6	mΩ
Dynamic chara	acteristics						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 30 \text{ V};$		-	14.8	-	nC
Q <sub>G(tot)</sub>	total gate charge	see <u>Figure 14</u> ; see <u>Figure 15</u>		-	70.8	-	nC
Avalanche rug	gedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS} = 10 \text{ V; } T_{j(init)} = 25 \text{ °C; } I_D = 100 \text{ A;}$ $V_{sup} \le 60 \text{ V; } R_{GS} = 50 \Omega; \text{ unclamped}$		-	-	266	mJ

<sup>[1]</sup> Continuous current is limited by package.



N-channel 60 V, 4.6 m $\Omega$  standard level MOSFET in TO220

### 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		<sub>G</sub> (EA)
mb	D	mounting base; connected to drain		mbb076 S
			SOT78 (TO-220AB)	

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN4R6-60PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

## 4. Marking

Table 4. Marking codes

Type number	Marking code
PSMN4R6-60PS	PSMN4R6-60PS

### 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		,			
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	60	V
$V_{DGR}$	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	60	V
$V_{GS}$	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 100 °C; see <u>Figure 1</u>	<u>[1]</u> _	99.7	Α
		T <sub>mb</sub> = 25 °C; see <u>Figure 1</u>	<u>[1]</u> _	100	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p = 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; see Figure 3	-	565	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	211	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	in diode				
Is	source current	T <sub>mb</sub> = 25 °C	[1] -	100	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p = 10 \mu s$ ; $T_{mb} = 25  ^{\circ}C$	-	565	Α
Avalanche i	ruggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup}$ ≤ 60 V; $R_{GS}$ = 50 $\Omega$ ; unclamped	-	266	mJ

#### [1] Continuous current is limited by package.

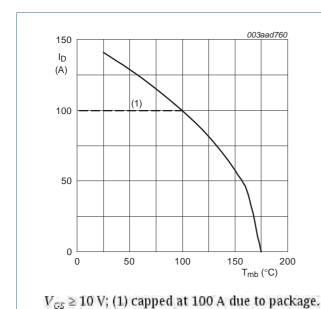
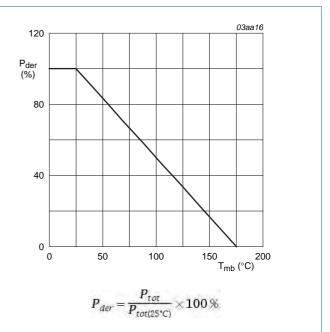


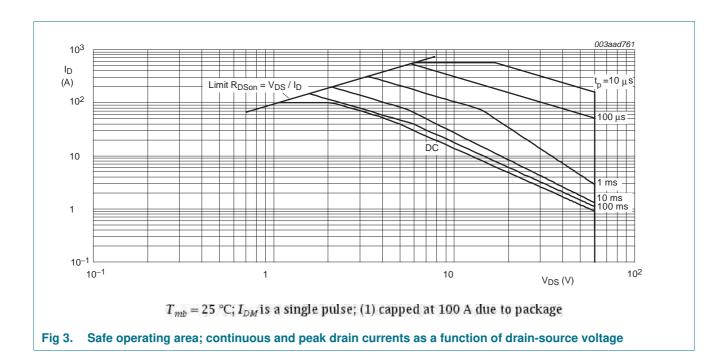
Fig 1. Continuous drain current as a function of mounting base temperature



ig 2. Normalized total power dissipation as a function of mounting base temperature

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### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.38	0.71	K/W

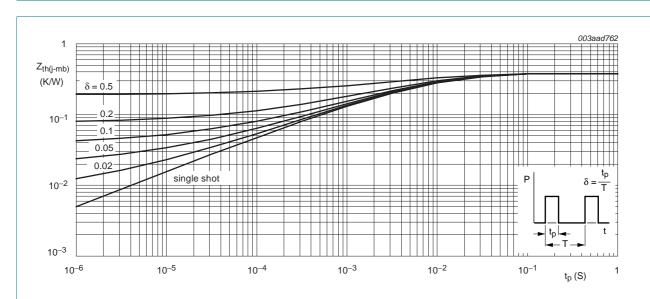


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values.

### 7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	54	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see Figure 11	-	-	4.6	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 175$ °C; see Figure 11	1	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	200	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 12	-	8.05	10.6	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C};$ see Figure 12	-	-	7.4	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	-	3.5	4.6	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	-	0.79	-	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 0$ A; $V_{DS} = 0$ V; $V_{GS} = 10$ V; see Figure 14	-	63	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$	-	70.8	-	nC
Q <sub>GS</sub>	gate-source charge	see Figure 14; see Figure 15	-	19.5	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14	-	13.5	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	6	-	nC
$Q_{GD}$	gate-drain charge	$I_D$ = 25 A; $V_{DS}$ = 30 V; $V_{GS}$ = 10 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	14.8	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	V <sub>DS</sub> = 30 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	4.3	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	4426	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	567	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	293	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	26	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	24	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	58	-	ns
t <sub>f</sub>	fall time		_	22	-	ns

Table 7. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drai	n diode					
V <sub>SD</sub>	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 17</u>	-	0.81	1.1	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ;	-	45	-	ns
Q <sub>r</sub>	recovered charge	$V_{DS} = 30 \text{ V}$	-	64	-	nC

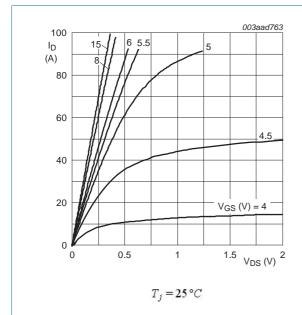


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

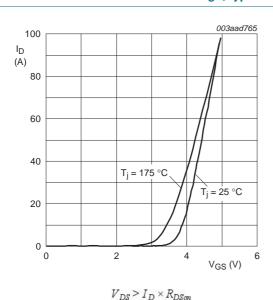
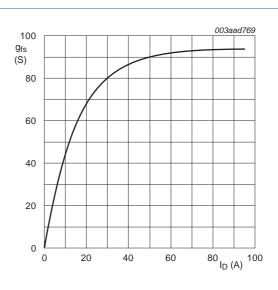
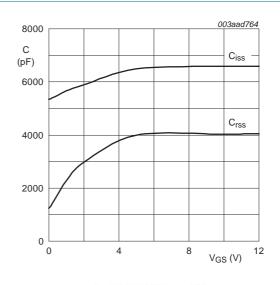


Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $T_j = 25 \, ^{\circ}\text{C}; V_{DS} = 10 \, \text{V}$ 

Fig 6. Forward transconductance as a function of drain current; typical values



 $f = 1 \text{ MHz}; V_{DS} = 0 \text{ V}$ 

Fig 8. Input and reverse transfer capacitances as a function of gate-source voltage, typical values

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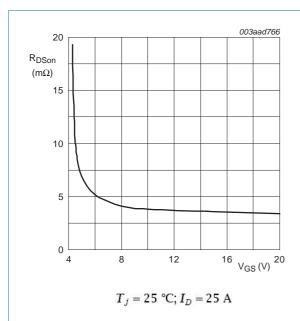


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

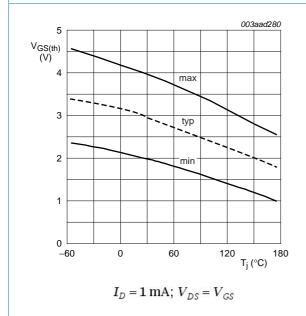
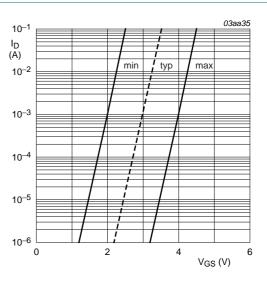


Fig 11. Gate-source threshold voltage as a function of junction temperature



 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$ 

Fig 10. Sub-threshold drain current as a function of gate-source voltage

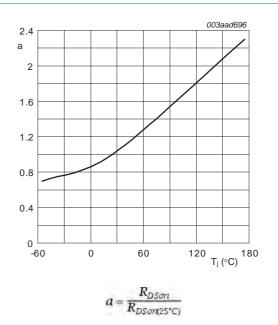


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature.

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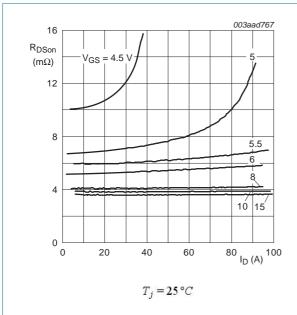


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

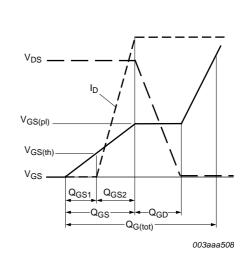


Fig 14. Gate charge waveform definitions

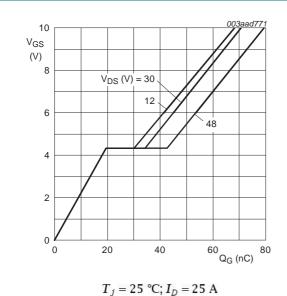
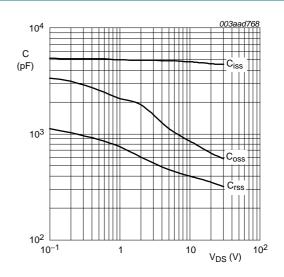


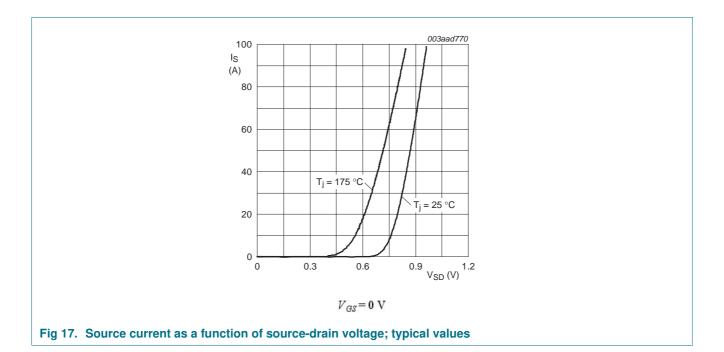
Fig 15. Gate-source voltage as a function of gate charge; typical values



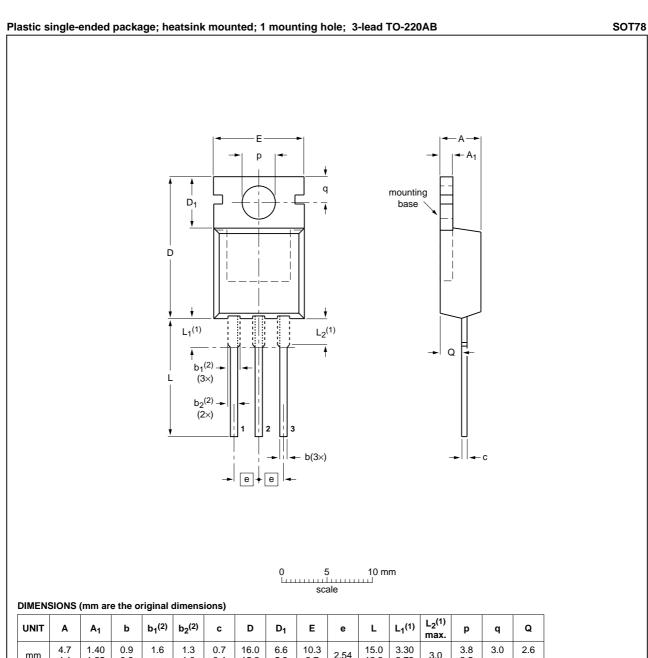
 $V_{GS} = 0 \text{ V}; \text{ f} = 1 \text{ MHz}$ 

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

N-channel 60 V, 4.6 m $\Omega$  standard level MOSFET in TO220



### Package outline



UNIT	A	A <sub>1</sub>	b	b <sub>1</sub> (2)	b <sub>2</sub> (2)	С	D	D <sub>1</sub>	E	е	L	L <sub>1</sub> (1)	L <sub>2</sub> <sup>(1)</sup> max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN ISSUE DATE		
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT78		3-lead TO-220AB	SC-46		<del>08-04-23</del> 08-06-13	

Fig 18. Package outline SOT78 (TO-220AB)

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N-channel 60 V, 4.6 mΩ standard level MOSFET in TO220

## 9. Revision history

### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN4R6-60PS v.3	20120418	Product data sheet	-	PSMN4R6-60PS v.2
Modifications:	<ul> <li>Various changes</li> </ul>	to content.		
PSMN4R6-60PS v.2	20101101	Product data sheet	-	PSMN4R6-60PS v.1

### 10. Legal information

#### 10.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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